The modulus chilled multiple PD

Yuri Dolganin, A.K. Dmitriev, I.I. Suri, M.A. Savchenko, V.N. Ovsyuk, V.P. Ezhov, V.V. Karpov, V.V. Vasilyev

Central Research Institute for Machine-Building
margun@tsniimash.ru

The results of operations to creation of moduluss matrix PD format 4\times(288\times4), topology - multirow bar, pixel – 25\times28 \text{ мкм}^2) are introduced. The justification of technological conditions of fabrication p-n in epitaxial and heteroepitaxial patterns with veryzone by strata is given. The construction of a photodetector is designed. The specification statement of the multiplexer for PD is reduced. The technological track p-n and construction of a photodetector is designed. The specification statement a construction of a cryostat, and also specification statement of gaging machinery is reduced. The following results are obtained: Is selected optimal, from the point of view of conditions of beaming, method of an ionic implantation conduction, applied for inverse, of patterns; The supervisory equipment of photoelectric arguments of photodetectors supplying measurings of responsiveness and threshold performances created, both experimental is model of countermeasure feelers, and multiple patterns, coincidence with the multiplexer; The studies are held and the trade - off of a construction PD is realized; The manufacturing process of fabrication of a photodiode array PD on a ground(basis) MIE MCT and chilled silicon multiplexer designed; The construction of a cryostat reducing wormstrum to PD up to 1,3\times1042;\times1090; is designed; Samples PD with arguments manufactured: - Mean specific detectivity in a maxima of spectral responsivity not less than 9,5\times10^{10}\text{ см Гц}^{1/2}\text{ Вт}^{-1}, - Wave length of a maxima of spectral responsiveness 9,8 microns,- Amount of the signal deductions - 8,- Working temperature - 80\times1050;,-V-W Responsiveness in maxima of spectral responsiveness at time of integrating 20 \mu s not less 8\times107 \text{ В / В}. 